MC14580B

4 x 4 Multiport Register

The MC14580B is a 4 by 4 multiport register useful in small scratch pad memories, arithmetic operations when coupled with an adder, and other data storage applications. It allows independent reading of any two words (or the same word at both outputs) while writing into any one of four words.

Address changing and data entry occur on the rising edge of the clock. When the write enable input is low, the contents of any word may be accessed but not altered.

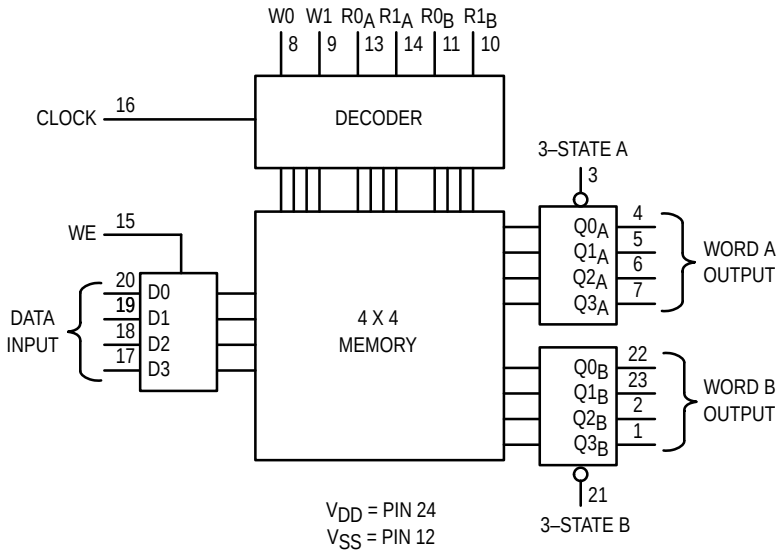
- No Restrictions on Clock Input Rise or Fall Times
- 3–State Outputs
- Single Phase Clocking
- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- Capable of Driving Two Low–power TTL Loads or one Low–power Schottky TTL Load Over the Rated Temperature Range
- Pin Compatible with CD40108

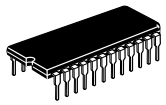
MAXIMUM RATINGS* (Voltages Referenced to V_{SS})

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage	– 0.5 to + 18.0	V
V_{in}, V_{out}	Input or Output Voltage (DC or Transient)	– 0.5 to V_{DD} + 0.5	V
I_{in}, I_{out}	Input or Output Current (DC or Transient), per Pin	± 10	mA
P_D	Power Dissipation, per Package†	500	mW
T_{stg}	Storage Temperature	– 65 to + 150	°C
T_L	Lead Temperature (8–Second Soldering)	260	°C

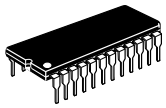
* Maximum Ratings are those values beyond which damage to the device may occur.
†Temperature Derating:
Plastic “P and D/DW” Packages: – 7.0 mW/°C From 65°C To 125°C
Ceramic “L” Packages: – 12 mW/°C From 100°C To 125°C

BLOCK DIAGRAM





L SUFFIX
CERAMIC
CASE 623



P SUFFIX
PLASTIC
CASE 709

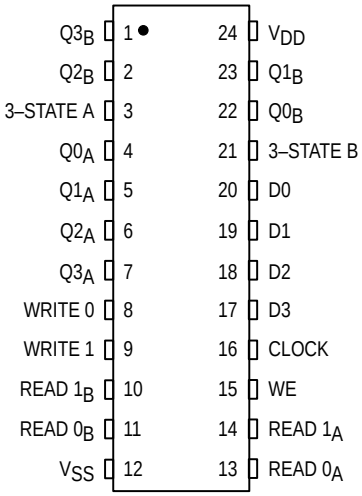
DW SUFFIX
SOIC
CASE 751E

ORDERING INFORMATION

MC14XXXBCP	Plastic
MC14XXXBCL	Ceramic
MC14XXXBDW	SOIC

T_A = – 55° to 125°C for all packages.

PIN ASSIGNMENT



REV 3
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ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	– 55°C Min	– 55°C Max	25°C Min	25°C Typ #	25°C Max	125°C Min	125°C Max	Unit
Output Voltage "0" Level V_{in} = V_{DD} or 0	V_{OL}	5.0 10 15	— — —	0.05 0.05 0.05	— — —	0 0 0	0.05 0.05 0.05	— — —	0.05 0.05 0.05	Vdc
"1" Level V_{in} = 0 or V_{DD}	V_{OH}	5.0 10 15	4.95 9.95 14.95	— — —	4.95 9.95 14.95	5.0 10 15	— — —	4.95 9.95 14.95	— — —	Vdc
Input Voltage "0" Level (V_O = 4.5 or 0.5 Vdc) (V_O = 9.0 or 1.0 Vdc) (V_O = 13.5 or 1.5 Vdc)	V_{IL}	5.0 10 15	— — —	1.5 3.0 4.0	— — —	2.25 4.50 6.75	1.5 3.0 4.0	— — —	1.5 3.0 4.0	Vdc
"1" Level (V_O = 0.5 or 4.5 Vdc) (V_O = 1.0 or 9.0 Vdc) (V_O = 1.5 or 13.5 Vdc)	V_{IH}	5.0 10 15	3.5 7.0 11	— — —	3.5 7.0 11	2.75 5.50 8.25	— — —	3.5 7.0 11	— — —	Vdc
Output Drive Current (V_{OH} = 2.5 Vdc) Source (V_{OH} = 4.6 Vdc) (V_{OH} = 9.5 Vdc) (V_{OH} = 13.5 Vdc)	I_{OH}	5.0 5.0 10 15	– 3.0 – 0.64 – 1.6 – 4.2	— — — —	– 2.4 – 0.51 – 1.3 – 3.4	– 4.2 – 0.88 – 2.25 – 8.8	— — — —	– 1.7 – 0.36 – 0.9 – 2.4	— — — —	mAdc
(V_{OL} = 0.4 Vdc) Sink (V_{OL} = 0.5 Vdc) (V_{OL} = 1.5 Vdc)	I_{OL}	5.0 10 15	0.64 1.6 4.2	— — —	0.51 1.3 3.4	0.88 2.25 8.8	— — —	0.36 0.9 2.4	— — —	mAdc
Input Current	I_{in}	15	—	±0.1	—	±0.00001	±0.1	—	±1.0	µAdc
Input Capacitance (V_{in} = 0)	C_{in}	—	—	—	—	5.0	7.5	—	—	pF
Quiescent Current (Per Package)	I_{DD}	5.0 10 15	— — —	5.0 10 20	— — —	0.010 0.020 0.030	5.0 10 20	— — —	150 300 600	µAdc
Total Supply Current**† (Dynamic plus Quiescent, Per Package) (C_L = 50 pF on all outputs, all buffers switching)	I_T	5.0 10 15	I_T = (1.18 µA/kHz) f + I_{DD} I_T = (1.91 µA/kHz) f + I_{DD} I_T = (2.67 µA/kHz) f + I_{DD}							µAdc
Three–State Leakage Current	I_{TL}	15	—	± 0.1	—	±0.0001	±0.1	—	±3.0	µAdc

#Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

** The formulas given are for the typical characteristics only at 25°C.

†To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50\ pF) + (C_L - 50)\ Vfk$$

where: I_T is in µA (per package), C_L in pF, V = (V_{DD} – V_{SS}) in volts, f in kHz is input frequency, and k = 0.004.

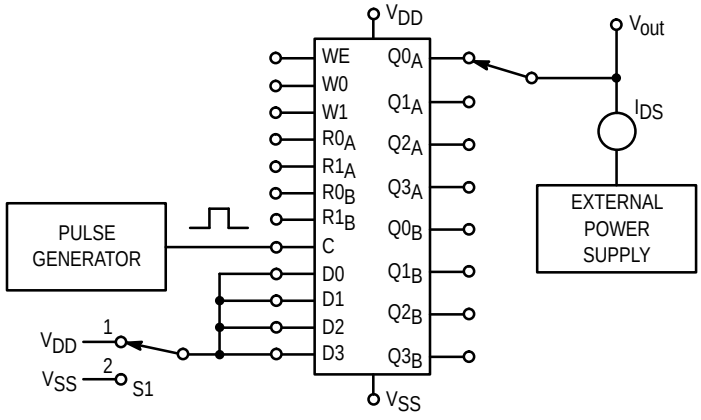
This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.

SWITCHING CHARACTERISTICS* (C_L = 50 pF, T_A = 25°C)

Characteristic	Symbol	V_{DD}	Min	Typ #	Max	Unit
Output Rise and Fall Time	t_{TLH}, t_{THL}					ns
t_{TLH}, t_{THL} = (1.5 ns/pF) C_L + 25 ns		5.0	—	100	200	
t_{TLH}, t_{THL} = (0.75 ns/pF) C_L + 12.5 ns	(Figures 3 and 6)	10	—	50	100	
t_{TLH}, t_{THL} = (0.55 ns/pF) C_L + 9.5 ns		15	—	40	80	
Propagation Delay Time	t_{PLH}, t_{PHL}	5.0	—	650	1300	ns
Clock to Output	(Figures 3 and 6)	10	—	250	500	
		15	—	170	340	
Write Enable Setup Time	t_{su}	5.0	800	400	—	ns
(Enabling a Write or Read)	(Figure 5)	10	300	150	—	
		15	200	100	—	
Write Enable Removal Time	t_{rem}	5.0	0	– 100	—	ns
(Disabling a Write or Read)	(Figure 5)	10	0	– 50	—	
		15	0	– 35	—	
Setup Time**	t_{su}	5.0	50	20	—	ns
Address, Data to Clock	(Figure 3)	10	30	0	—	
		15	25	0	—	
Hold Time**	t_h	5.0	480	160	—	ns
Clock to Address, Data	(Figure 3)	10	195	65	—	
		15	150	50	—	
3–State Enable/Disable Delay Time	t_{PHZ}, t_{PLZ}	5.0	—	130	260	ns
	t_{PZH}, t_{PZL}	10	—	60	120	
	(Figures 4 and 7)	15	—	45	90	
Clock Pulse Width	t_w	5.0	820	410	—	ns
	(Figure 3)	10	330	165	—	
		15	220	110	—	

** When loading repetitive highs, the output may glitch low momentarily after the rising edge of Clock. However, data integrity remains unaffected and data is valid after the propagation delays listed in the Switching Characteristics Table.



	Sink Current	Source Current
Position of S1	2	1
V_{GS} =	V_{DD}	$-V_{DD}$
V_{DS} =	V_{out}	$V_{out} - V_{DD}$

Figure 1. Output Drive Current Test Circuit

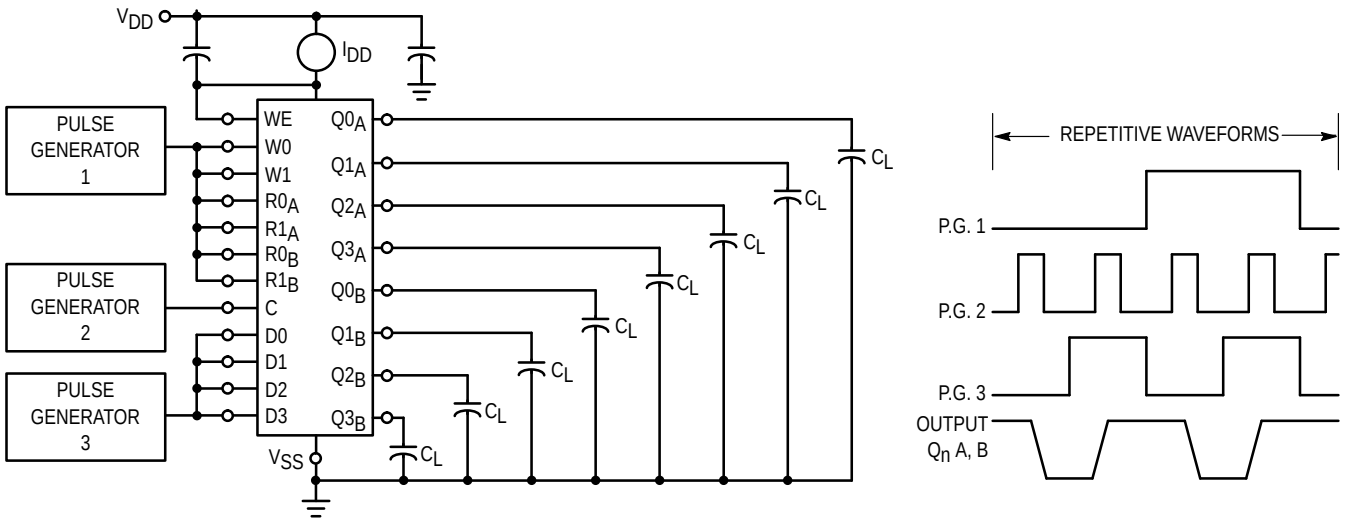


Figure 2. Power Dissipation Test Circuit and Waveforms (3–State Inputs are High)

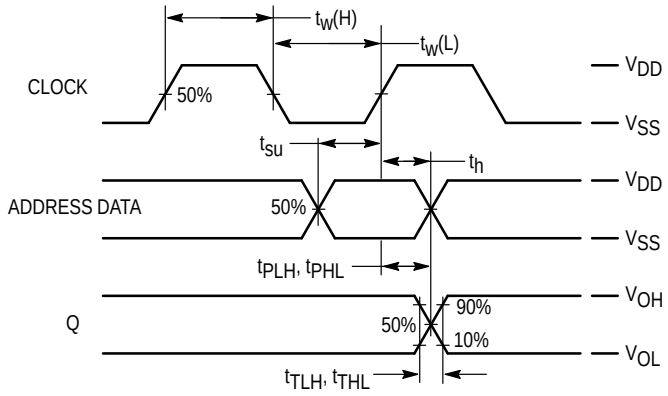


Figure 3.

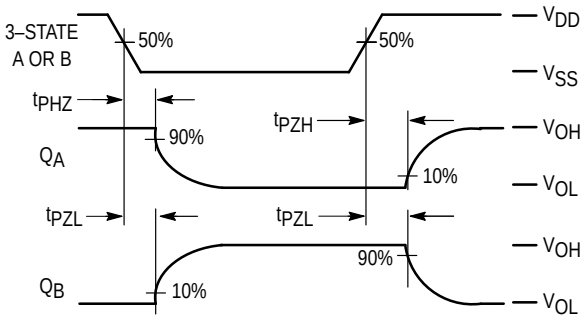


Figure 4.

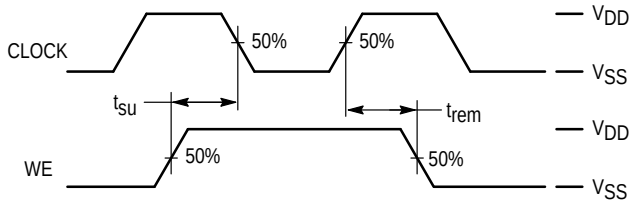


Figure 5.

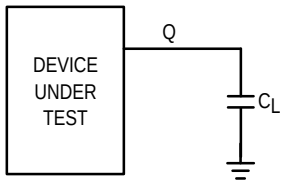


Figure 6. Test Circuit

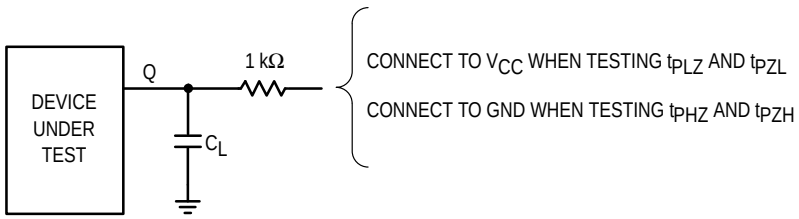
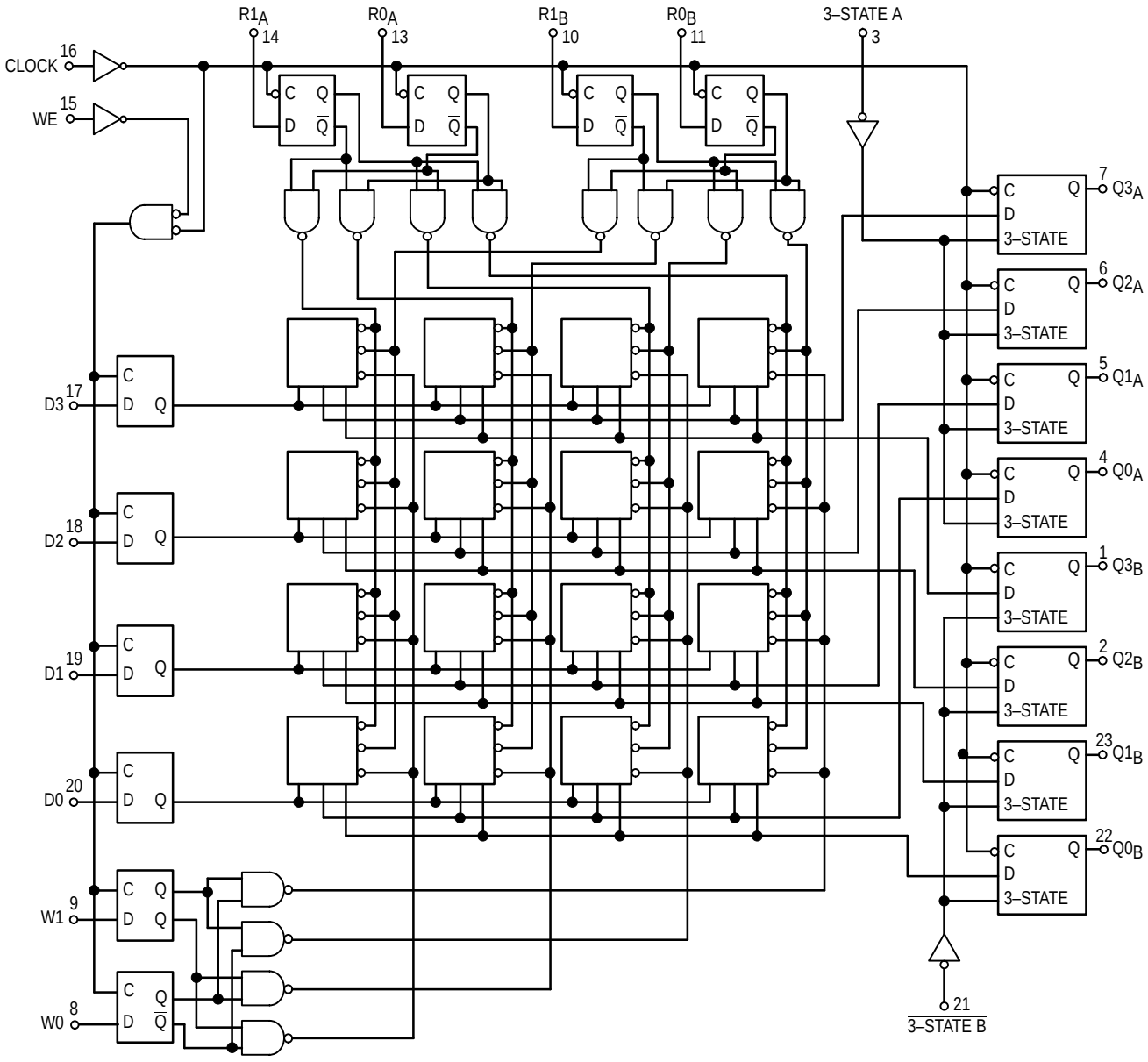


Figure 7. Test Circuit

LOGIC DIAGRAM



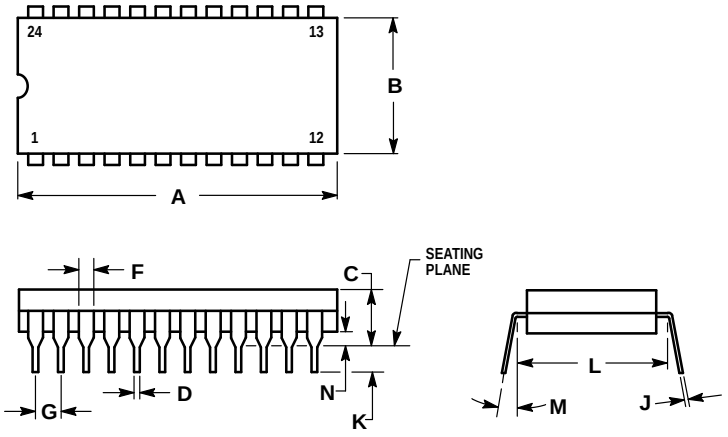
TRUTH TABLE

Clock	WE	Write 1	Write 0	Read 1_A	Read 0_A	Read 1_B	Read 0_B	3–State A	3–State B	D_n	Q_nA	Q_nB
↗	1	0	1	0	1	0	1	1	1	1	1	1
↗	1	0	1	0	1	0	1	1	1	0	0	0
↘	X	X	X	X	X	X	X	1	1	X	No Change	No Change
X	X	X	X	X	X	X	X	0	0	X	Z	Z
0	X	X	X	X	X	X	X	1	1	X	No Change	No Change
1	X	X	X	X	X	X	X	1	1	X	No Change	No Change
↗	1	0	0	0	1	1	0	1	1	D_n to word 0	Contents of word 1 displayed	Contents of word 2 displayed
↗	0	0	0	0	1	1	0	1	1	Word 0 not altered	Contents of word 1 displayed	Contents of word 2 displayed

Z = High Impedance
X = Don't Care

OUTLINE DIMENSIONS

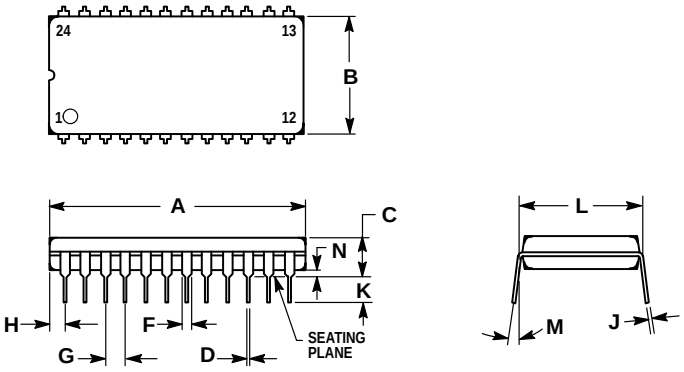
L SUFFIX
CERAMIC DIP PACKAGE
CASE 623–05
ISSUE M



NOTES:
1. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
2. LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE POSITION AT SEATING PLANE AT MAXIMUM MATERIAL CONDITION (WHEN FORMED PARALLEL).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	31.24	32.77	1.230	1.290
B	12.70	15.49	0.500	0.610
C	4.06	5.59	0.160	0.220
D	0.41	0.51	0.016	0.020
F	1.27	1.52	0.050	0.060
G	2.54 BSC		0.100 BSC	
J	0.20	0.30	0.008	0.012
K	3.18	4.06	0.125	0.160
L	15.24 BSC		0.600 BSC	
M	0 °	15 °	0 °	15 °
N	0.51	1.27	0.020	0.050

P SUFFIX
PLASTIC DIP PACKAGE
CASE 709–02
ISSUE C

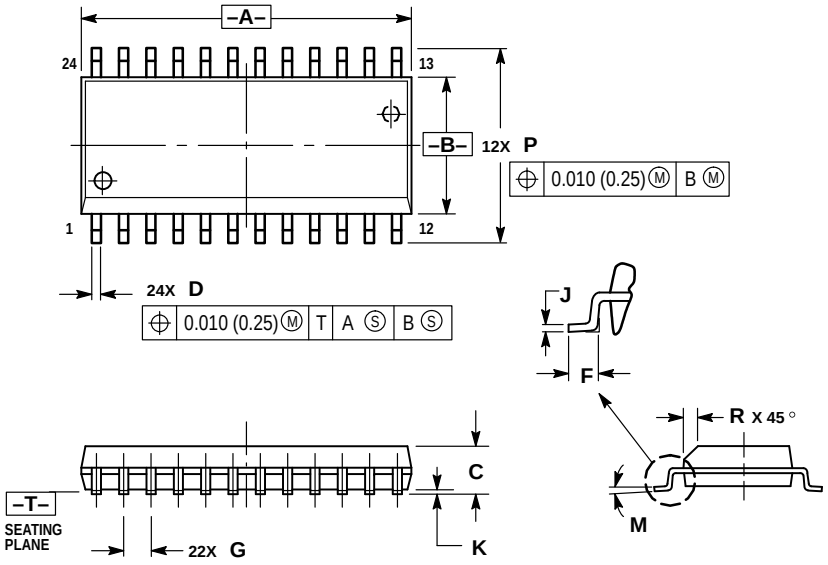


NOTES:
1. POSITIONAL TOLERANCE OF LEADS (D), SHALL BE WITHIN 0.25 (0.010) AT MAXIMUM MATERIAL CONDITION, IN RELATION TO SEATING PLANE AND EACH OTHER.
2. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
3. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	31.37	32.13	1.235	1.265
B	13.72	14.22	0.540	0.560
C	3.94	5.08	0.155	0.200
D	0.36	0.56	0.014	0.022
F	1.02	1.52	0.040	0.060
G	2.54 BSC		0.100 BSC	
H	1.65	2.03	0.065	0.080
J	0.20	0.38	0.008	0.015
K	2.92	3.43	0.115	0.135
L	15.24 BSC		0.600 BSC	
M	0 °	15 °	0 °	15 °
N	0.51	1.02	0.020	0.040

OUTLINE DIMENSIONS

DW SUFFIX
PLASTIC SOIC PACKAGE
CASE 751E–04
ISSUE E



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.13 (0.005) TOTAL IN EXCESS OF D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	15.25	15.54	0.601	0.612
B	7.40	7.60	0.292	0.299
C	2.35	2.65	0.093	0.104
D	0.35	0.49	0.014	0.019
F	0.41	0.90	0.016	0.035
G	1.27 BSC		0.050 BSC	
J	0.23	0.32	0.009	0.013
K	0.13	0.29	0.005	0.011
M	0 °	8 °	0 °	8 °
P	10.05	10.55	0.395	0.415
R	0.25	0.75	0.010	0.029

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